



15N10

Power MOSFET

14.7A, 100V (D-S) N-CANNEL POWER MOSFET

DESCRIPTION

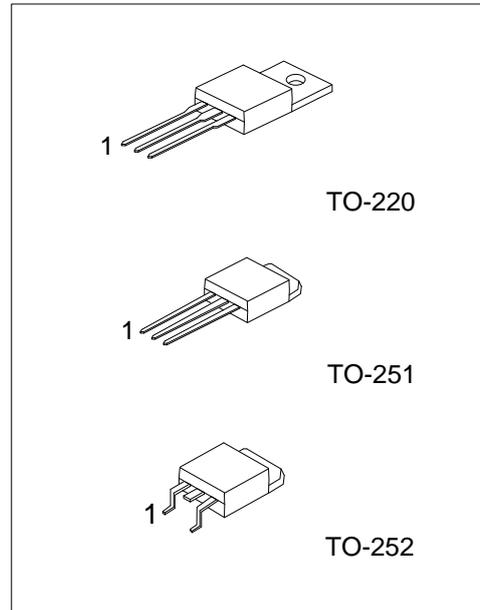
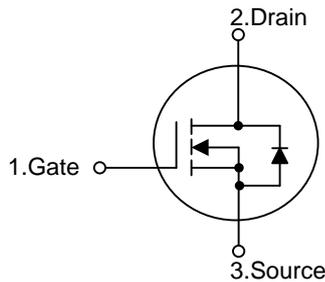
The UTC 15N10 is an N-Channel enhancement MOSFET, it uses UTC's advanced technology to provide customers with a minimum on-state resistance, high switching speed and low gate charge.

The UTC 15N10 is suitable for high efficiency switching DC/DC converter, LCD display inverter and load switch.

FEATURES

- * $R_{DS(ON)} \leq 100 \text{ m}\Omega @ V_{GS}=10\text{V}, I_D=8.0\text{A}$
- $R_{DS(ON)} \leq 110 \text{ m}\Omega @ V_{GS}=4.5\text{V}, I_D=8.0\text{A}$
- * High switching speed

SYMBOL



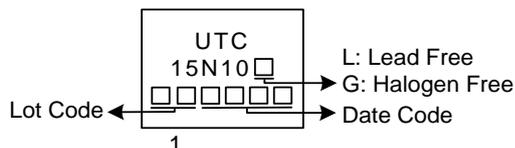
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
15N10L-TA3-T	15N10G-TA3-T	TO-220	G	D	S	Tube
15N10L-TM3-T	15N10G-TM3-T	TO-251	G	D	S	Tube
15N10L-TN3-R	15N10G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>15N10G-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TM3: TO-251, TN3: TO-252</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
---	--

MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GSS}	±20	V
Drain Current	Continuous	T _C =25°C	I _D	14.7	A
		T _C =70°C		13.6	A
	Pulsed		I _{DM}	30	A
Power Dissipation	T _C =25°C	TO-220	P _D	60	W
		TO-251		34.7	W
		TO-252			
Operating Junction Temperature			T _J	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220	θ _{JA}	62.5	°C/W
	TO-251/TO-252		110	°C/W
Junction to Case (Note)	TO-220	θ _{JC}	2.5	°C/W
	TO-251/TO-252		3.6 (Note)	°C/W

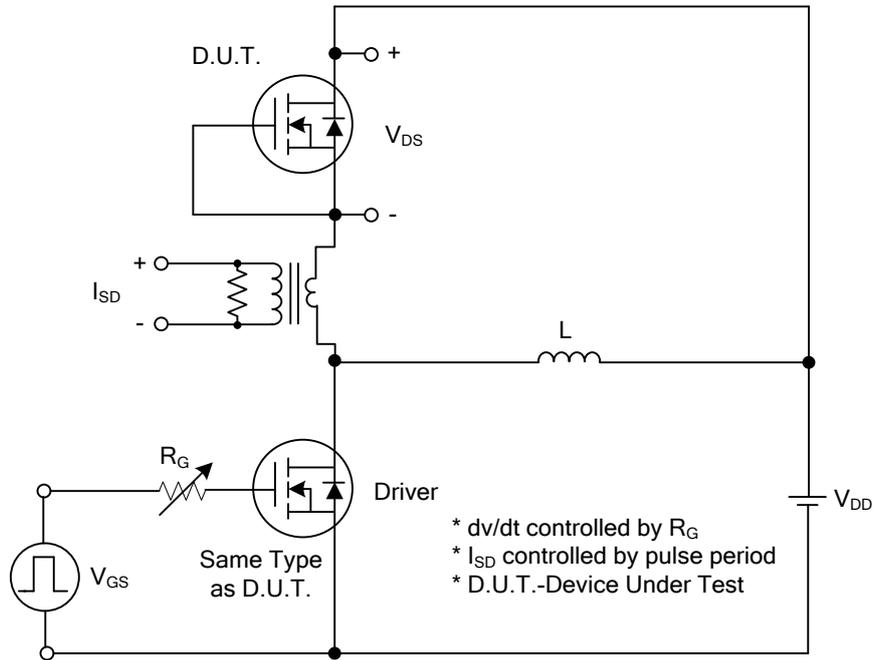
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

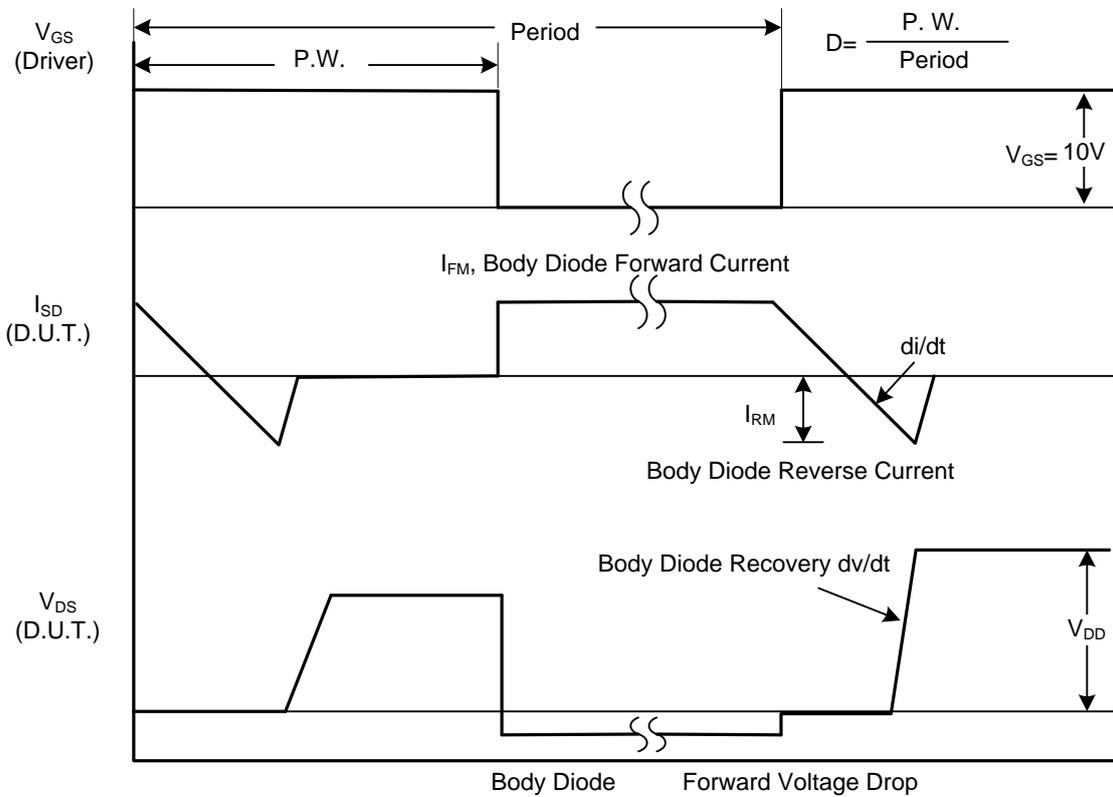
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	100			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =+20V, V _{DS} =0V			+100	nA
		V _{GS} =-20V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	1.0		3.0	V
Drain-Source On-State Resistance (Note)	R _{DS(ON)}	V _{GS} =10V, I _D =8.0A			100	mΩ
		V _{GS} =4.5V, I _D =8.0A			110	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =15V, f=1MHz		1411		pF
Output Capacitance	C _{OSS}			78		pF
Reverse Transfer Capacitance	C _{RSS}			65		pF
Gate-Resistance	R _G	V _{DS} =0V, V _{GS} =0V, f=1MHz		0.81		Ω
SWITCHING PARAMETERS						
Total Gate Charge	Q _G	V _{GS} =10V, V _{DS} =80V, I _D =15A		34		nC
Total Gate Charge	Q _G	V _{GS} =4.5V, V _{DS} =80V, I _D =15A		18.4		nC
Gate to Source Charge	Q _{GS}			5.5		nC
Gate to Drain Charge	Q _{GD}			8		nC
Turn-ON Delay Time	t _{D(ON)}			13		ns
Rise Time	t _R	V _{DS} =50V, V _{GS} =10V, I _D =15A, R _G =25Ω		22		ns
Turn-OFF Delay Time	t _{D(OFF)}			100		ns
Fall-Time	t _F			43		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V _{SD}	I _S =8A, V _{GS} =0V		0.9	1.2	V

Note: Pulse test: pulse width ≤ 300us, duty cycle ≤ 2%, Guaranteed by design, not subject to production testing.

■ TEST CIRCUITS AND WAVEFORMS

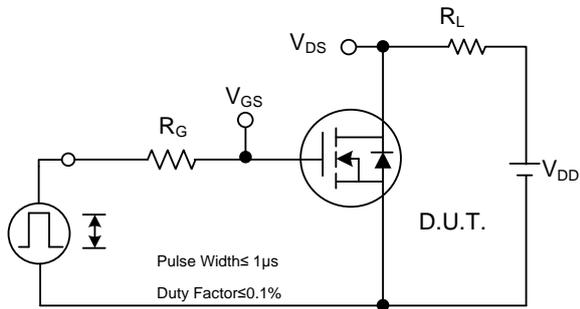


Peak Diode Recovery dv/dt Test Circuit

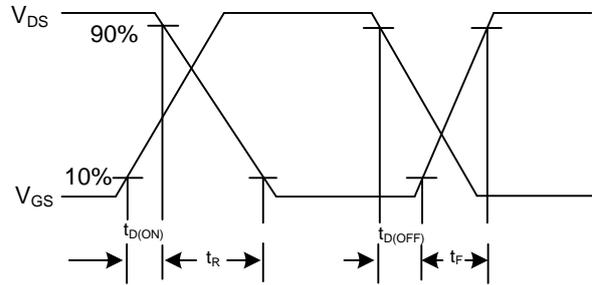


Peak Diode Recovery dv/dt Waveforms

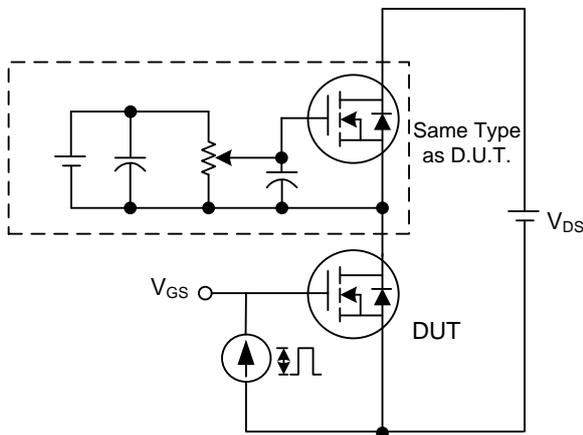
TEST CIRCUITS AND WAVEFORMS



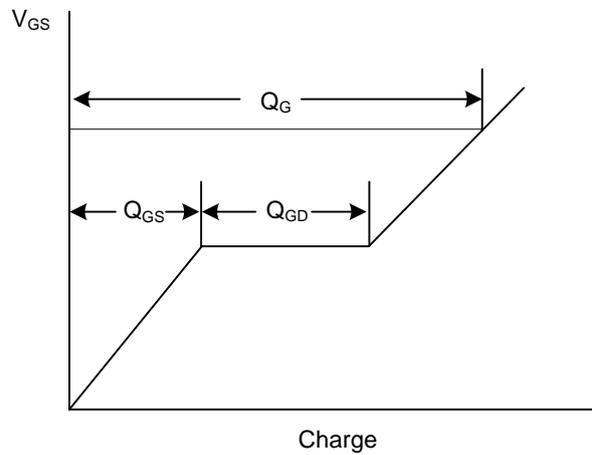
Switching Test Circuit



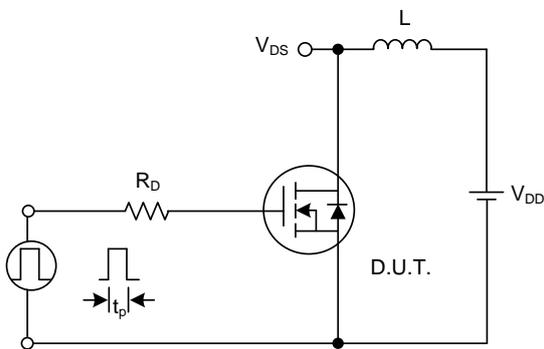
Switching Waveforms



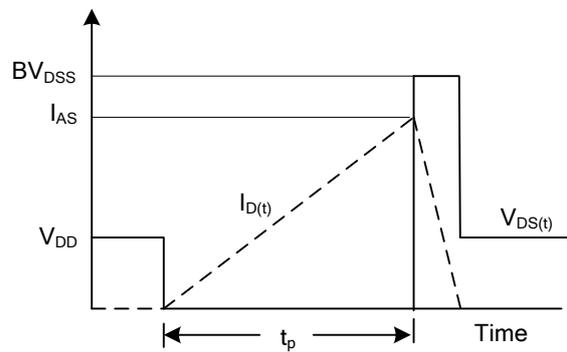
Gate Charge Test Circuit



Gate Charge Waveform

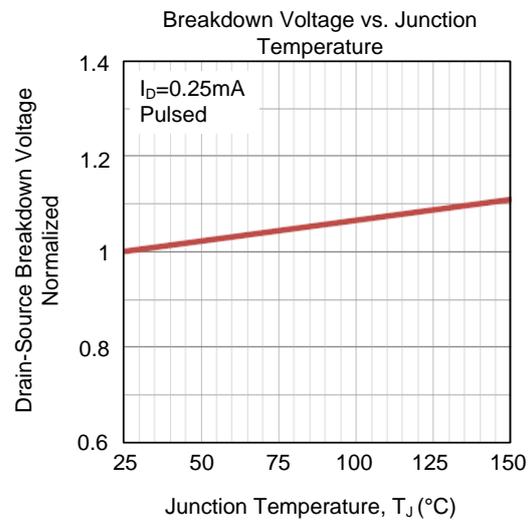
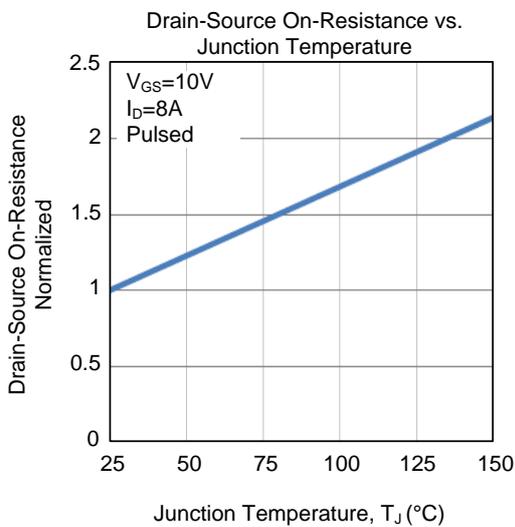
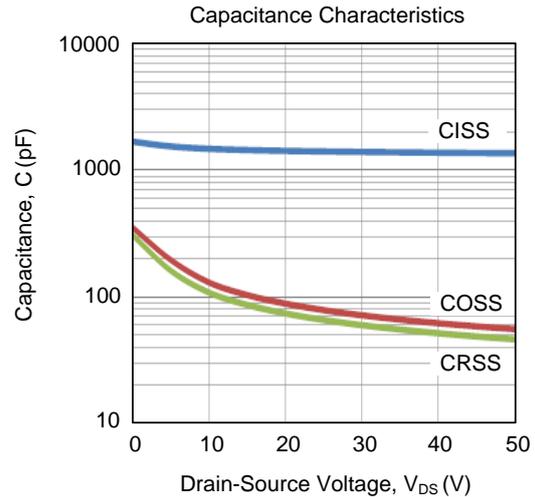
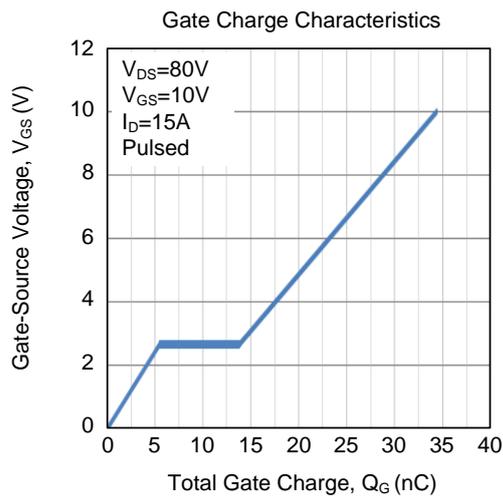
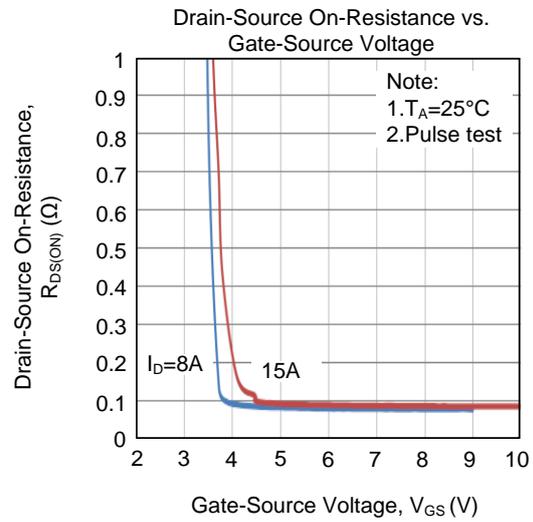
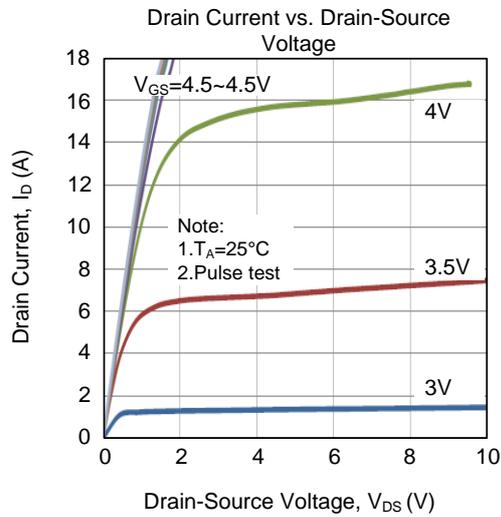


Unclamped Inductive Switching Test Circuit

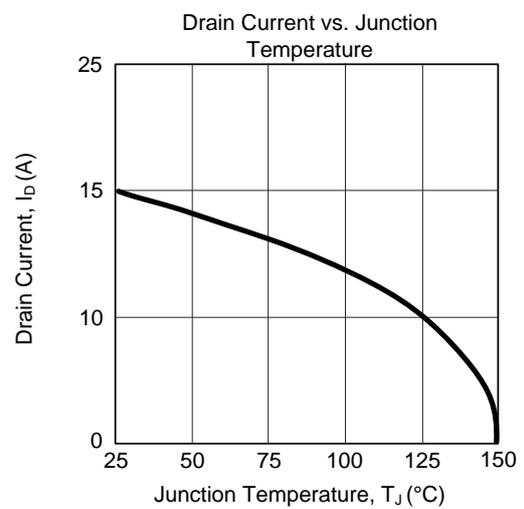
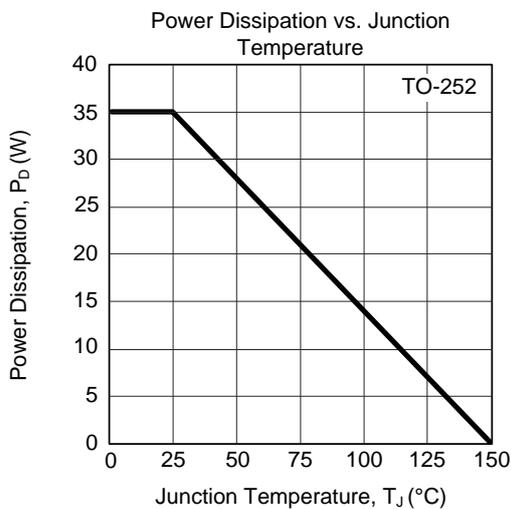
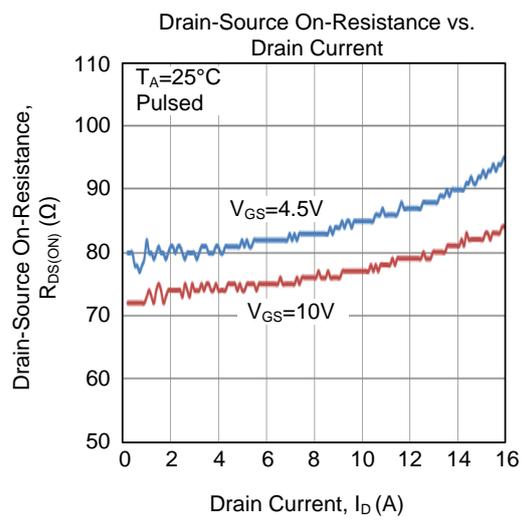
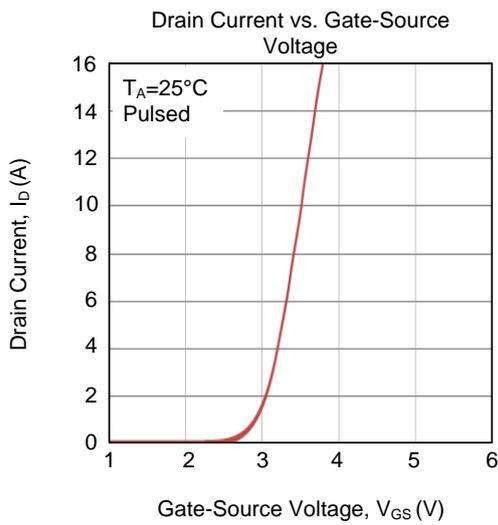
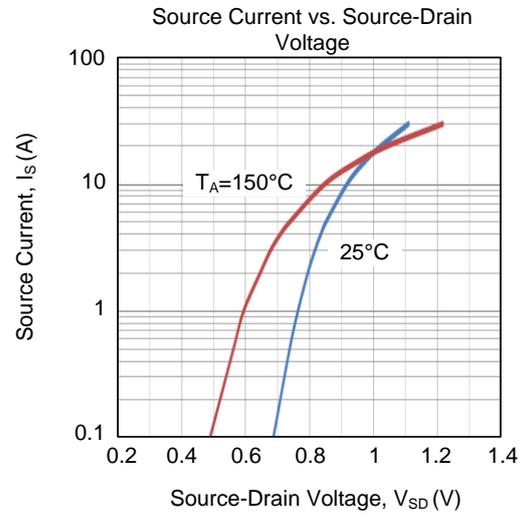
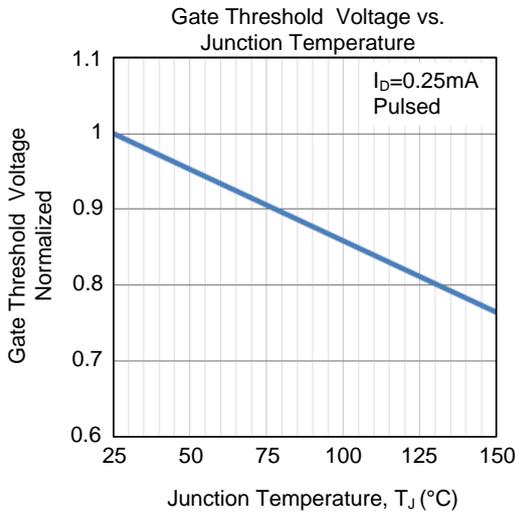


Unclamped Inductive Switching Waveforms

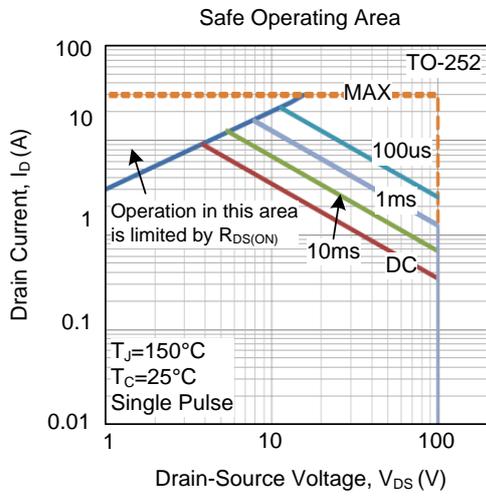
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ **TYPICAL CHARACTERISTICS (Cont.)**



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.